VS-HFA70FA120

Vishay Semiconductors



HEXFRED[®] Ultrafast Soft Recovery Diode, 70 A



PRIMARY CHARACTERISTICS						
V _R 1200 V						
V _F (typical)	2.3 V					
t _{rr} (typical)	51 ns					
$I_{F(AV)}$ per module at T_C	70 A at 94 °C					
Package	SOT-227					

FEATURES

- · Fast recovery time characteristic
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- · Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

The dual diode series configuration (VS-HFA70FA120) is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V _R		1200	V		
Continuous forward current per leg	١ _F	T _C = 110 °C	35	٨		
Single pulse forward current per leg	I _{FSM}	$T_J = 25 \ ^{\circ}C$	380	A		
Maximum power dissipation per module	PD	T _C = 110 °C	174	W		
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 min	2500	V		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA	1200	-	-		
Forward voltage	V _{FM}	I _F = 30 A	-	2.30	3.00	V	
		I _F = 60 A	-	2.89	3.80		
		I _F = 30 A, T _J = 125 °C	-	2.14	2.44		
		I _F = 60 A, T _J = 125 °C	-	2.82	3.27		
	I _{RM}	$V_{R} = V_{R}$ rated	-	1.2	75	μA	
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1.0	-	mA	
		$T_J = 150 \ ^{\circ}C, V_R = V_R \text{ rated}$	-	2.7	10	IIIA	

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}; dI_F/d$	t = 200 A/ μ s; V _R = 30 V	-	51	-		
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 50 A dI _F /dt = - 200 A/μs V _R = 200 V	-	134	-	ns A	
		T _J = 125 °C		-	204	-		
Pools recovery ourrent	I _{RRM}	$T_J = 25 \ ^\circ C$		-	12	-		
Peak recovery current		T _J = 125 °C		-	18	-		
	Q _{rr}	T _J = 25 °C		-	790	-	nC	
Reverse recovery charge		T _J = 125 °C		-	1770	-	no	
Junction capacitance	CT	V _R = 1200 V		-	24	-	pF	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Junction to case, single leg conducting	D		-	-	0.46			
Junction to case, both legs conducting	R _{thJC}		-	-	0.23	°C/W		
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.10	-			
Weight			-	30	-	g		
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)		
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)		
Case style				SOT	-227			

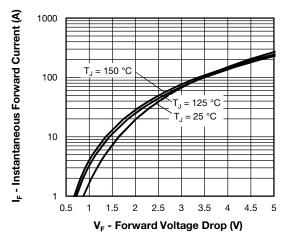


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

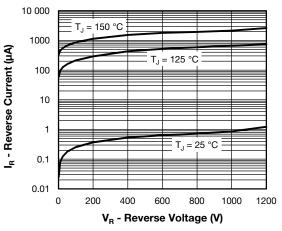


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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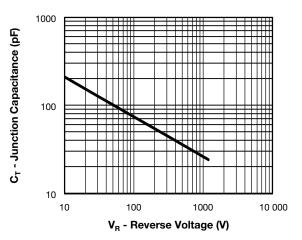


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

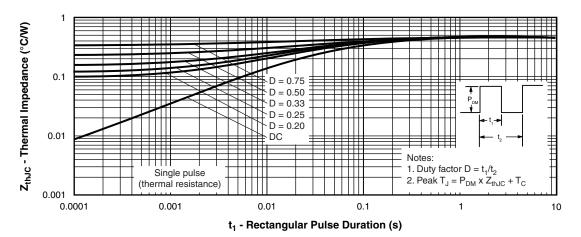
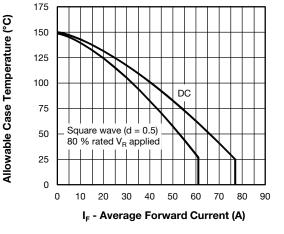
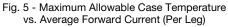


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)





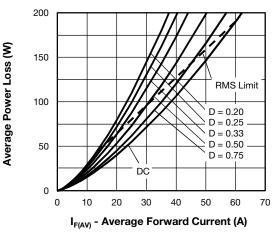


Fig. 6 - Forward Power Losses Characteristics (Per Leg)

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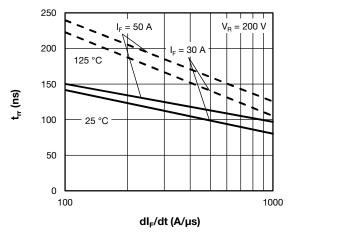
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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

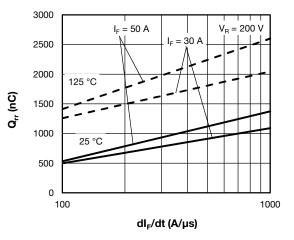


Fig. 8 - Typical Stored Charge vs. dl_F/dt

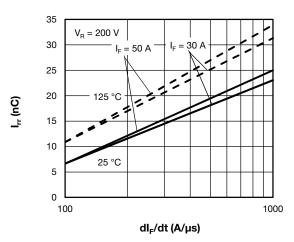


Fig. 9 - Typical Reverse Recovery Current vs. dI_F/dt

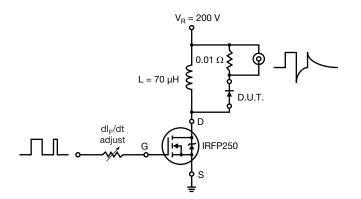
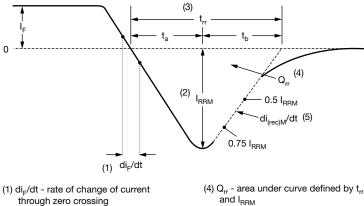


Fig. 10 - Reverse Recovery Parameter Test Circuit

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- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_E to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.

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and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code

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`	vs-	HF	Α	70	F	Α	120		
(2	3	4	5	6	7		
	 Vishay Semiconductors product HEXFRED[®] family 								
3	- 1	Pro	Process designator (A = electron irradiated)						
4		Cur	Current rating (70 = 70 A)						
5	-	Circ	Circuit configuration (two separate diodes, parallel pin-out)						
6	-	Pac	Package indicator (SOT-227 standard insulated base)						

Voltage rating (120 = 1200 V)

CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Two separate diodes, parallel pin-out	F	Lead Assignment 4 0 0 3 4 1 0 0 2 1 1 0 0 2 2 2				

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95423						
Packaging information	www.vishay.com/doc?95425					
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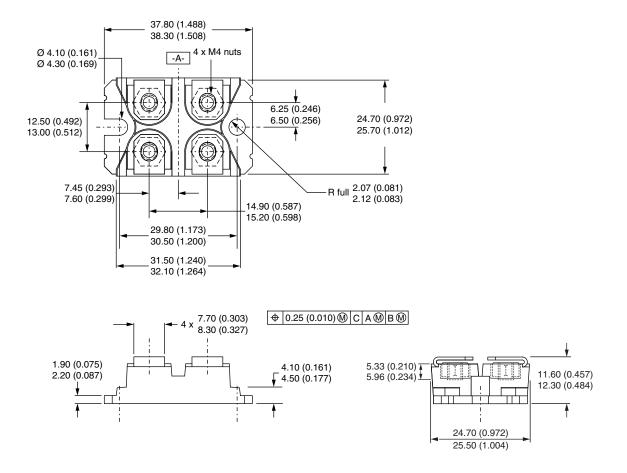
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SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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